

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (canceled)
2. (canceled)
3. (canceled)
4. (canceled)
5. (canceled)
6. (canceled)
7. (canceled)
8. (canceled)
9. (canceled)
10. (canceled)

11. (previously presented) A semiconductor integrated circuit device comprising:

trenches formed in a semiconductor substrate and defining active regions and dummy regions; and

element isolation insulating films buried in said trenches by polishing an insulating layer formed over said trenches and said semiconductor substrate such that said element isolation insulating films serve as element isolation regions,

wherein said dummy regions are formed at a scribing area.

12. (previously presented) A semiconductor integrated circuit device according to claim 11, wherein a length of said dummy region is shorter than a distance between external terminals.

13. (previously presented) A semiconductor integrated circuit device comprising:
trenches formed in a semiconductor substrate and defining active regions and dummy regions; and
insulating films buried in said trenches by polishing an insulating layer formed over said trenches and said semiconductor substrate such that said insulating films serve as element isolation insulating films;
wherein said dummy regions are formed at a scribing area.

14. (previously presented) A semiconductor integrated circuit device according to claim 13, wherein a length of said dummy region is shorter than a distance between bonding pads.

15. (previously presented) A semiconductor integrated circuit device comprising:
trenches formed in a semiconductor substrate and defining active regions and dummy regions; and
element isolation insulating films buried in said trenches by polishing an insulating layer formed over said trenches and said semiconductor substrate,
wherein said dummy regions are formed at a scribing area.

16. (previously presented) A semiconductor integrated circuit device according to claim 15, wherein a length of said dummy region is shorter than a distance between external terminals.

17. (new) A semiconductor integrated circuit device comprising:

a trench formed in a semiconductor substrate and defining active regions and dummy regions;

element isolation insulating films buried in said trench such that said element isolation insulating films serve as element isolation regions;

an interlayer insulating film covering said substrate and dummy regions and comprising a planarized insulating film; and

external terminals formed over said interlayer insulating film such that said dummy regions are formed under said external terminals.

18. (new) A semiconductor integrated circuit device according to claim 17, wherein a length of said dummy region is shorter than a distance between said external terminals.